

80V N-Channel Power MOSFET

DESCRIPTION

The MP150N08 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

Application

- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply

KEY CHARACTERISTICS

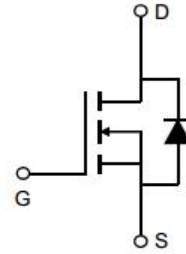
- $V_{DS} = 80V, I_D = 155A$
 $R_{DS(ON)} < 4.0m\Omega @ V_{GS}=10V$
- High density cell design for lower R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation

100% UIS TESTED!

100% DVDS TESTED!



TO-220 Top Vi



Schematic diagram

Package Marking And Ordering Information

Device Marking	Ordering Codes	Package	Product Code	Packing
150N08	MP150N08-P	TO-220	150N08	Tube

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	155	A
Drain Current-Pulsed (Note 1)	I_{DM}	823	A
Maximum Power Dissipation ($T_C=25^\circ C$)	P_D	259	W
Single pulse avalanche energy (Note 2)	E_{AS}	823	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.7	$^\circ C/W$
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	80	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3	4	V
Drain-Source On-State Resistance ^(Note 3)	$R_{DS(on)}$	$V_{GS}=10V, I_D=80A$	-	4	5	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=50V, I_D=75A$	-	180	-	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V,$ $f=1.0MHz$	-	4115	-	pF
Output Capacitance	C_{oss}		-	570	-	pF
Reverse Transfer Capacitance	C_{rss}		-	395	-	pF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=40V, I_D=40A,$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	28	-	nS
Turn-on Rise Time	t_r		-	20	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	50	-	nS
Turn-Off Fall Time	t_f		-	23	-	nS
Total Gate Charge	Q_g	$V_{DS}=40V, I_D=40A$ $V_{GS}=10V$	-	69	-	nC
Gate-Source Charge	Q_{gs}		-	23	-	nC
Gate-Drain Charge	Q_{gd}		-	22	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=155A$	-	-	1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. EAS condition : $T_j=25^\circ C, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25\Omega$
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production.

Characteristics Curves

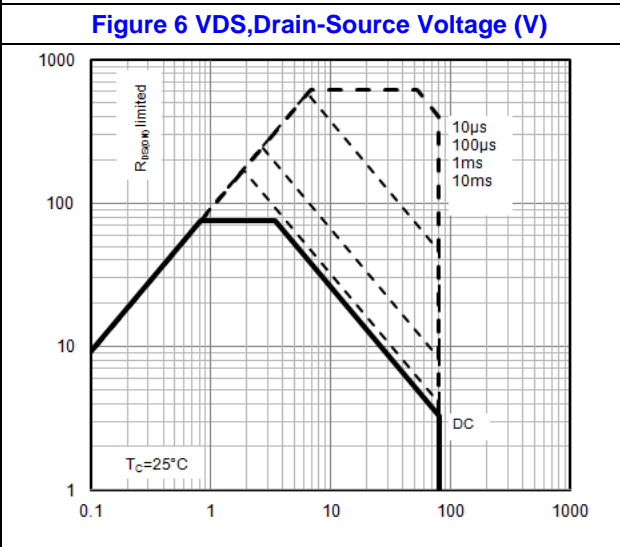
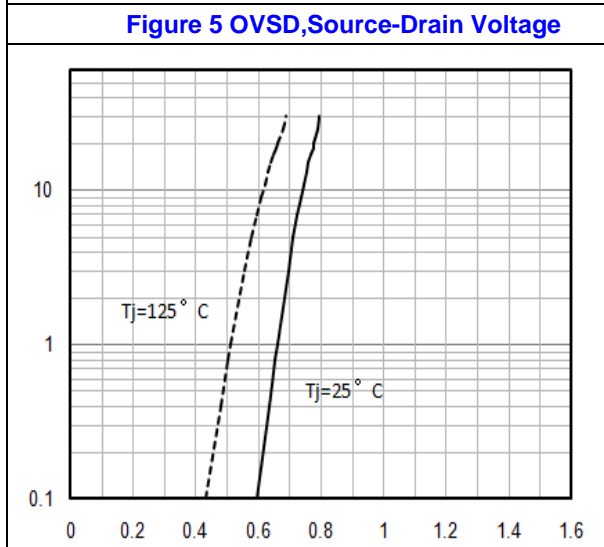
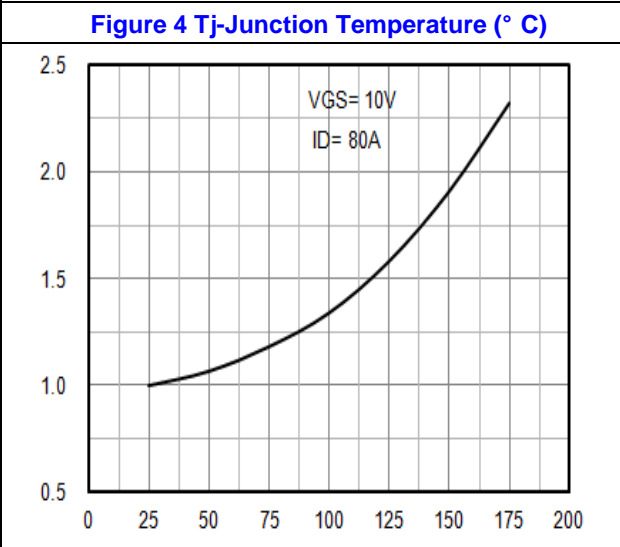
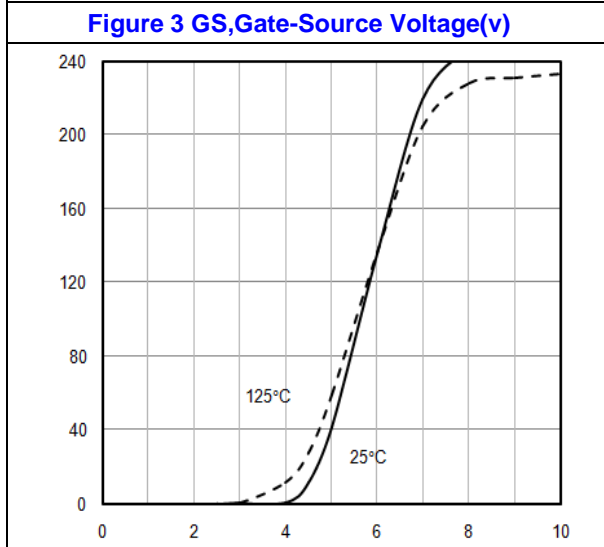
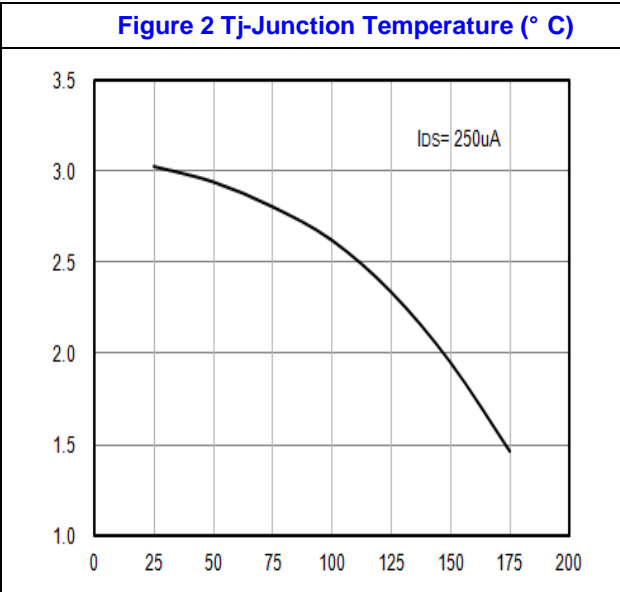
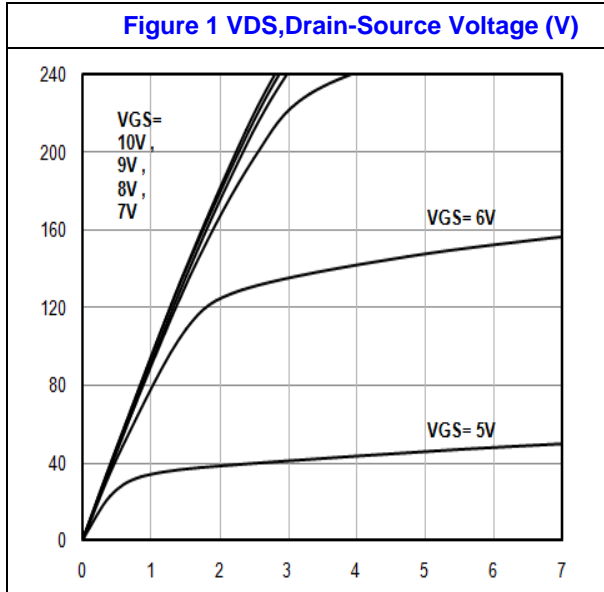


Figure 7 VDS, Drain-Source Voltage (V)

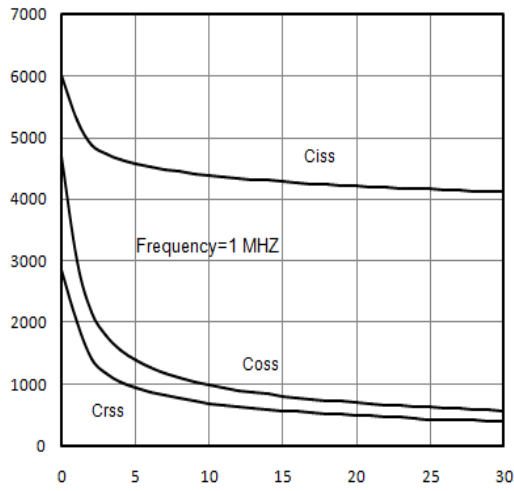


Figure 8 Qg-Total Gate Charge (nC)

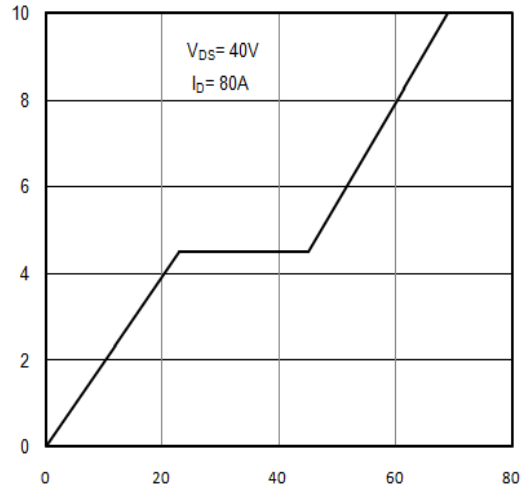
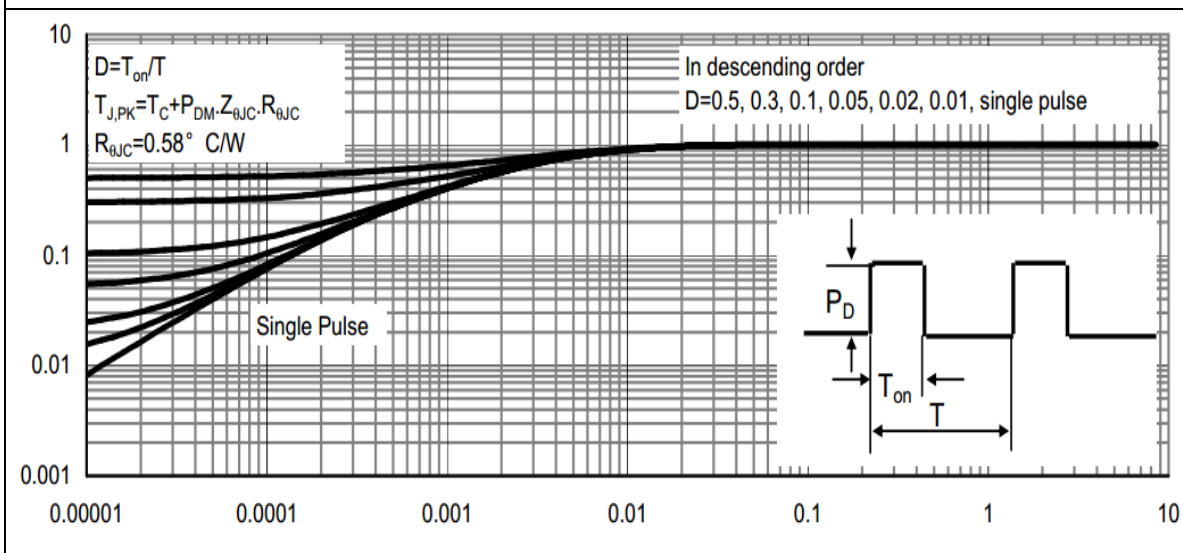


Figure 9. Normalized Maximum Transient Thermal Impedance



Test Circuit and Waveform

Figure 10. Unclamped Inductive Test Circuit and waveforms

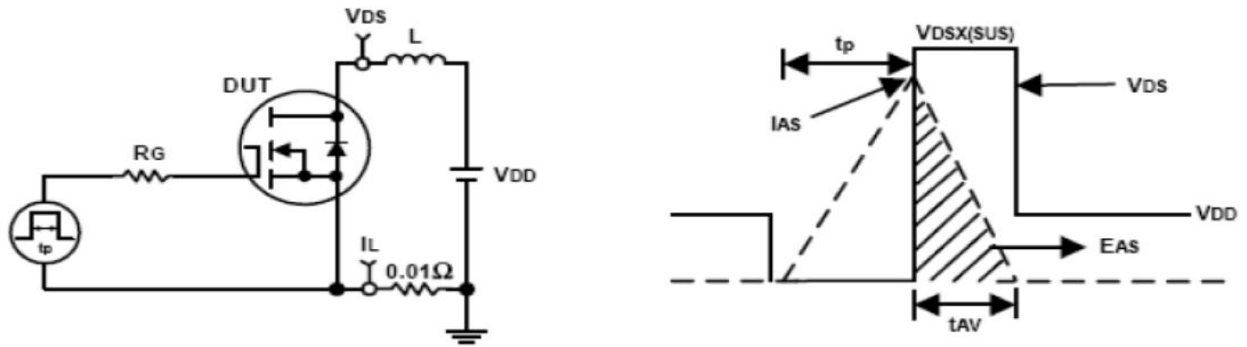
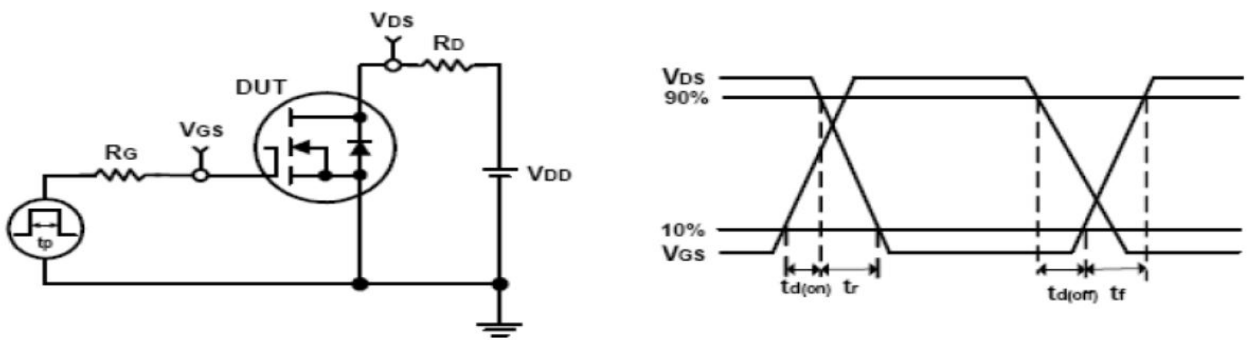
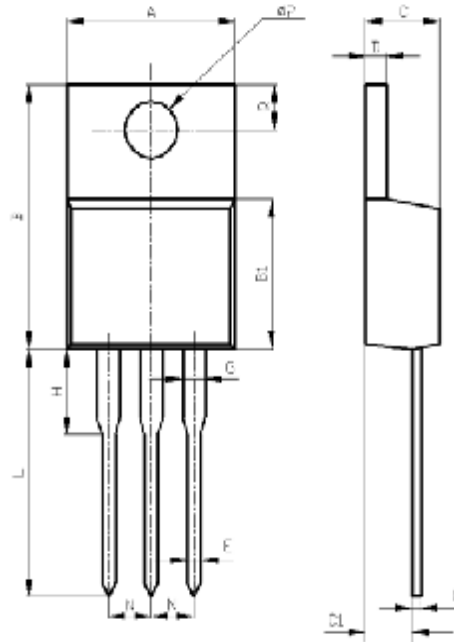


Figure 11. Switching Time Test Circuit and waveforms



Package Description



Items	Values(mm)	
	MIN	MAX
A	9.60	10.6
B	15.0	16.0
B1	8.90	9.50
C	4.30	4.80
C1	2.30	3.10
D	1.20	1.40
E	0.70	0.90
F	0.30	0.60
G	1.17	1.37
H	2.70	3.80
L	12.6	14.8
N	2.34	2.74
Q	2.40	3.00
ϕP	3.50	3.90

TO-220 Package